100V N-Channel SGT Power MOSFET

General Description

The SJD045N10 uses SGT technology to provide excellent $R_{DS(ON)}$, low gate charge and fast switching characteristics. This device is suitable for use as a wide variety of applications.

Features

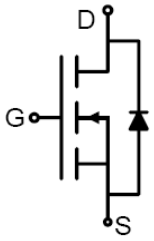
- Low Gate Charge
- 100% UIS Tested, 100% DVDS Tested
- High Power and current handing capability
- Lead free product is acquired

Application

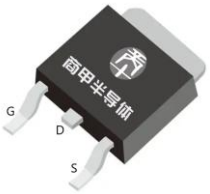
- DC/DC Converter
- Ideal for high-frequency switching and synchronous rectification

Key Performance Parametes

Parameter	Value	Unit
V_{DS}	100	V
$R_{DS(ON)\_TYP}$	5	mΩ
I_D	122	A
Q_G	47	nC



Schematic Diagram



TO-220 top view

RoHS

Package Marking and Ordering Information

Device/Ordering Code	Marking	Package	Packing	Reel Size	Tape width	Quantity
SJD045N10	SJD045N10	TO-252	Tube	\	\	2500 Pcs

Table 1. Absolute Maximum Ratings (T_C=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	100	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±20	V
I_D	Drain Current-Continuous(T_C=25℃)	122	A
	Drain Current-Continuous(T_C=100℃)	77	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	488	A
P_D	Maximum Power Dissipation(T_C=25℃)	171	W
	Maximum Power Dissipation(T_C=100℃)	68	W
E_{AS}	Avalanche energy (Note 2)	576	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		0.73	℃/W

Table 3. Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	100			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=60V, V_{GS}=0V T_J=25℃			1	μA
		V_{DS}=60V, V_{GS}=0V T_J=125℃			100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=250μA	2		4	V
g_{FS}	Forward Transconductance	V_{DS}=5V, I_D=20A		28		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=10V, I_D=20A T_J=25℃		5	6.2	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=25V,V_{GS}=0V, f=1.0MHz		2944		pF
C_{oss}	Output Capacitance			1551		pF
C_{rss}	Reverse Transfer Capacitance			71.9		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1.0MHz		1.7		Ω
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=10V, V_{DS}=50V, R_L=2.5Ω, R_{GEN}=6Ω		22.4		nS
t_r	Turn-on Rise Time			6.6		nS
$t_{d(off)}$	Turn-Off Delay Time			33.2		nS
t_f	Turn-Off Fall Time			7.6		nS
Q_g	Total Gate Charge	V_{GS}=10V, V_{DS}=50V, I_D=20A		47		nC
Q_{gs}	Gate-Source Charge			14.2		nC
Q_{gd}	Gate-Drain Charge			9.8		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				122	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=20A			1.2	V
t_{rr}	Reverse Recovery Time	I_F=20A, dI/dt=100A/μs		49.2		ns
Q_{rr}	Reverse Recovery Charge	I_F=20A, dI/dt=100A/μs		54.1		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=50V,V_G=10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

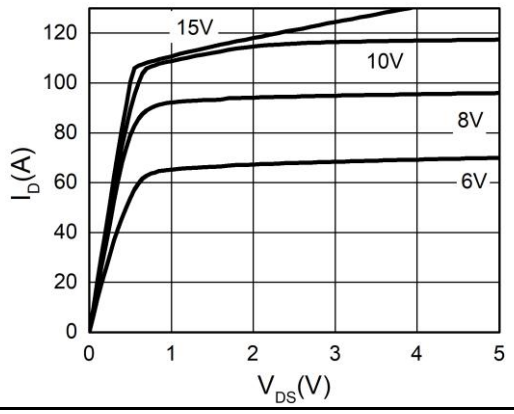


Figure 2. Transfer Characteristics

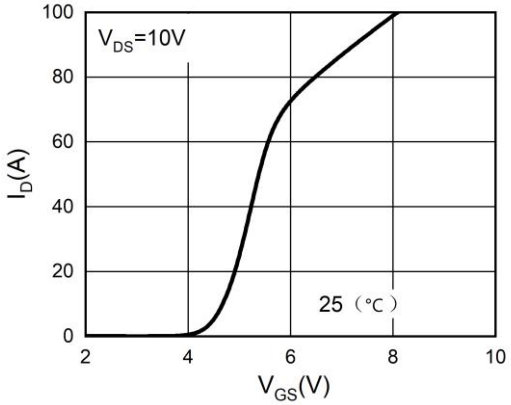


Figure 3. Power Dissipation

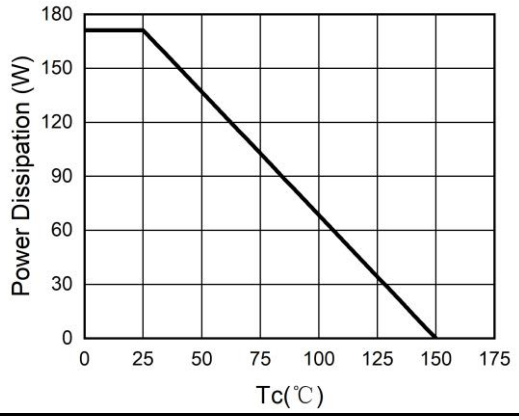


Figure 4. Drain Current

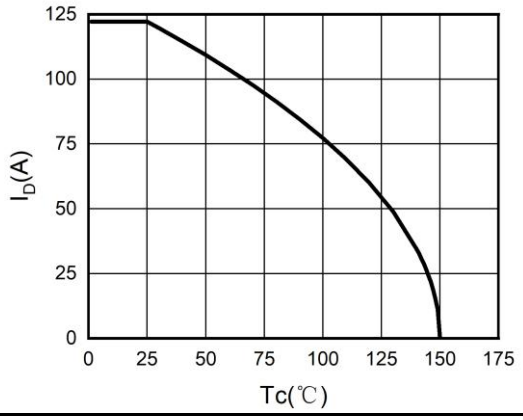


Figure 5. BV_{DSS} vs Junction Temperature

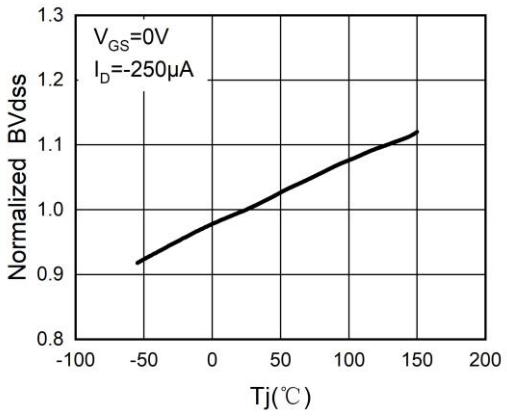
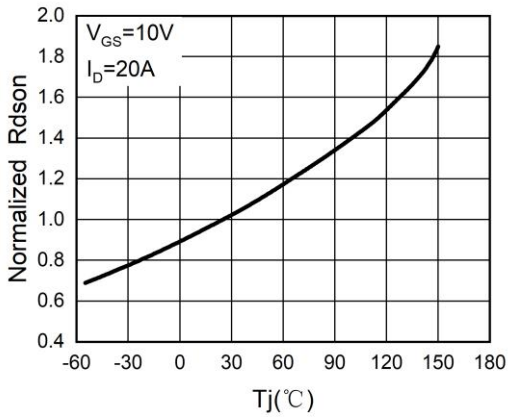


Figure 6. $R_{DS(ON)}$ vs Junction Temperature



Typical Electrical And Thermal Characteristics (Curves)

Figure 7. Gate Charge Waveforms

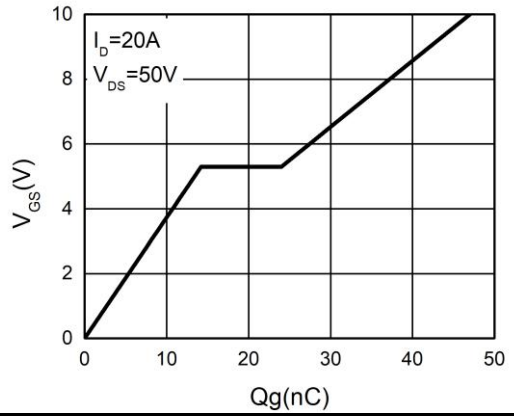


Figure 8. Capacitance

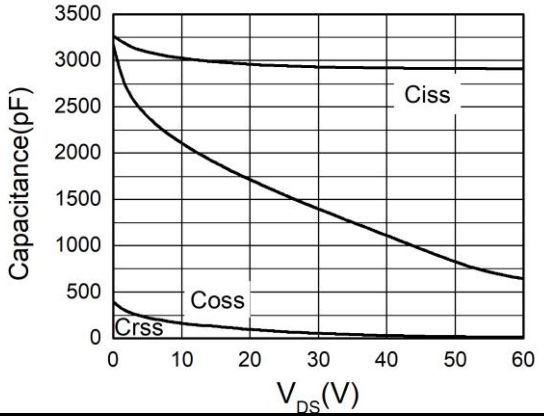


Figure 9. Body-Diode Characteristics

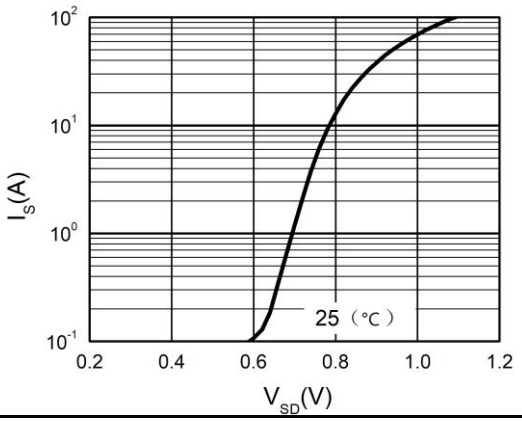
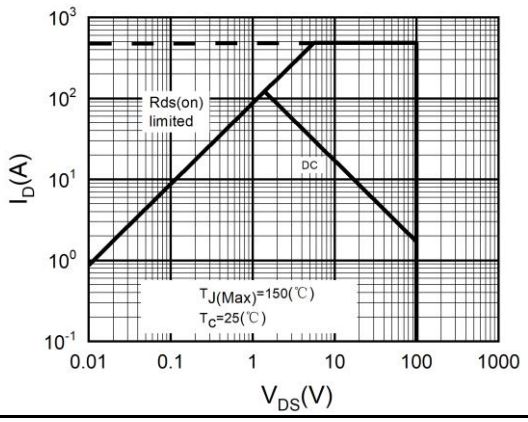
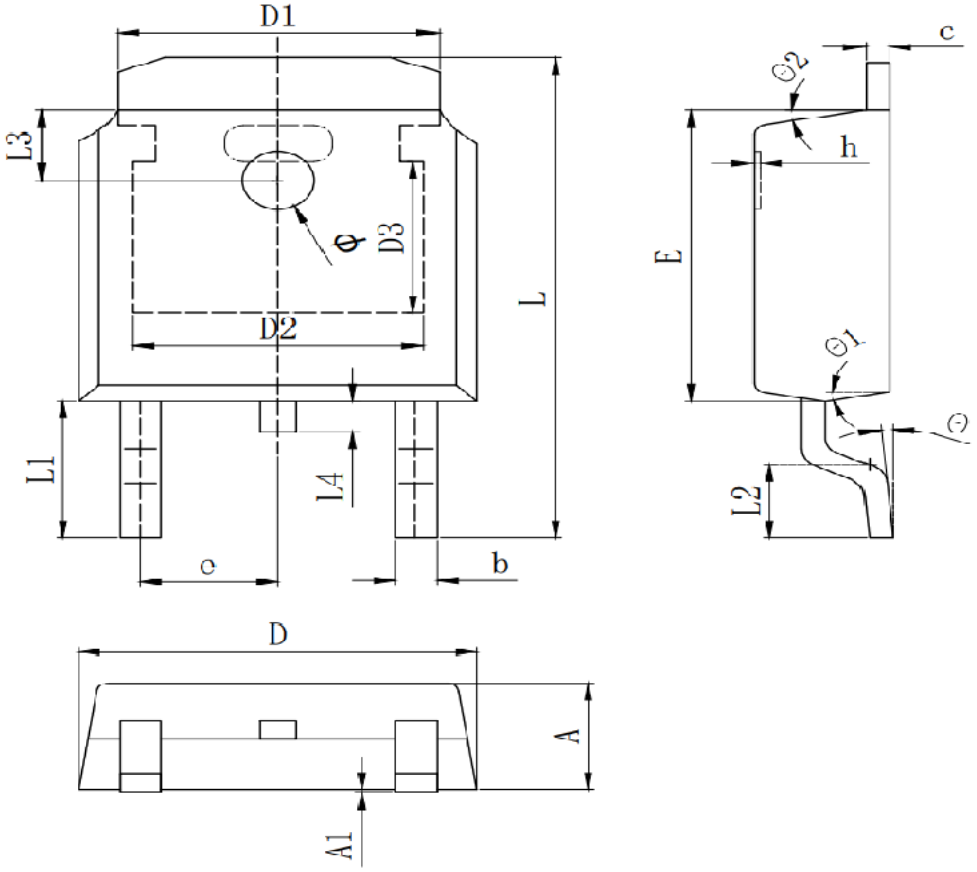


Figure 10. Maximum Safe Operating Area



TO-252 Package Information



Symbol	Dimensions In Millimeters		
	Min.	Typ.	Max.
A	2.200	2.300	2.400
A1	0.000		0.127
b	0.640	0.690	0.740
c(电镀后)	0.460	0.520	0.580
D	6.500	6.600	6.700
D1	5.334 REF		
D2	4.826 REF		
D3	3.166 REF		
E	6.000	6.100	6.200
e	2.286 TYP		
h	0.000	0.100	0.200
L	9.900	10.100	10.300
L1	2.888 REF		
L2	1.400	1.550	1.700
L3	1.600 REF		
L4	0.600	0.800	1.000
Φ	1.100	1.200	1.300
θ	0°		8°
θ1	9° TYP		
θ2	9° TYP		

Attention

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